

HSS100

FEATURES :

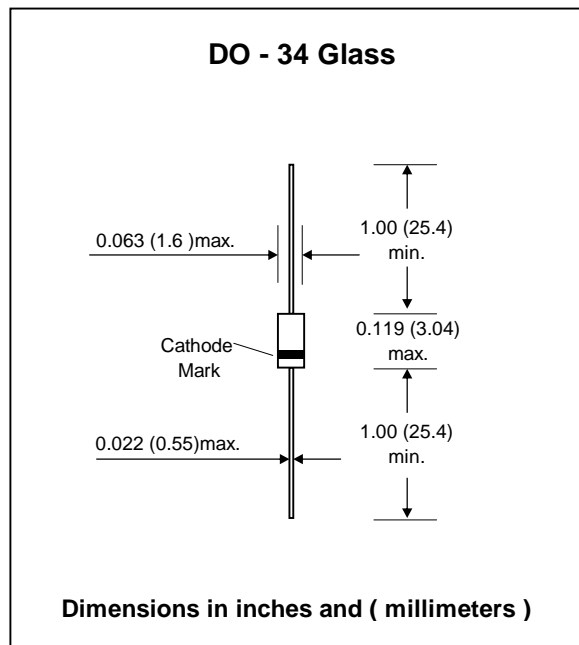
- Very Low I_R
- Low V_F and high efficiency.
- Pb / RoHS Free

MECHANICAL DATA :

Case: DO-34 Glass Case

Weight: approx. 0.11g

SCHOTTKY BARRIER DIODE



Maximum Ratings and Thermal Characteristics (Rating at 25 °C ambient temperature unless otherwise specified.)

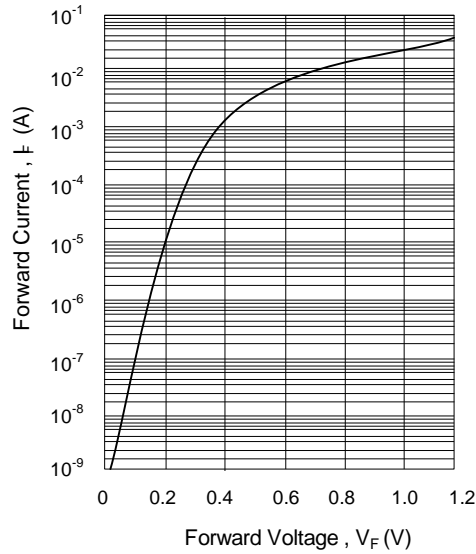
Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	60	V
Average Rectified Current	I_o	35	mA
Power Dissipation	P_D	150	mW
Junction Temperature	T_J	125	°C
Storage temperature range	T_{stg}	-65 to + 125	°C

Electrical Characteristics (Ta = 25°C unless otherwise noted)

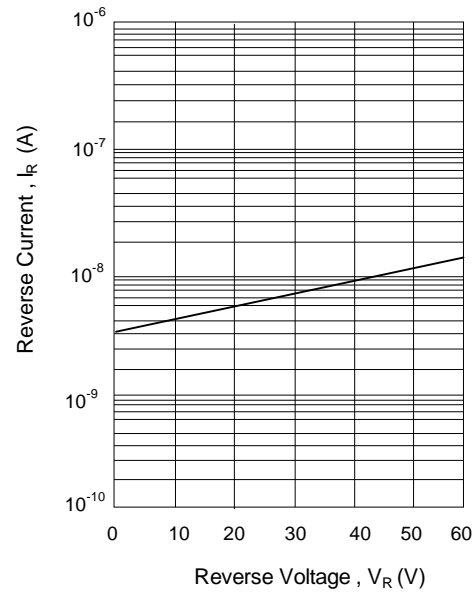
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Current	I_R	$V_R = 50 V$	-	-	100	nA
Reverse Voltage	V_R	$I_R = 10 \mu A$	60	-	-	V
Forward Voltage	V_F	$I_F = 10 mA$	-	-	0.42	V
		$I_F = 20 mA$	-	-	0.90	V
Diode Capacitance	C_d	$V_R = 0V, f = 1MHz$	-	-	2.2	pF
Diode Capacitance Deviation	ΔC_d	$V_R = 0V, f = 1MHz$	-	-	0.2	pF
Forward Voltage Deviation	ΔV_F	$I_F = 20 mA$	-	-	10	mV

RATING AND CHARACTERISTIC CURVES (HSS100)

Forward Current VS. Forward Voltage



Reverse Current VS. Reverse Voltage



Diode capacitance VS. Reverse Voltage

